

2N6050 2N6051 2N6052 PNP
 2N6057 2N6058 2N6059 NPN

**COMPLEMENTARY SILICON
 DARLINGTON POWER
 TRANSISTORS**



TO-3 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N6050, 2N6057 series types are complementary silicon Darlington power transistors, manufactured by the epitaxial base process, designed for high gain amplifier and switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$)

Collector-Base Voltage
 Collector-Emitter Voltage
 Emitter-Base Voltage
 Continuous Collector Current
 Peak Collector Current
 Continuous Base Current
 Power Dissipation
 Operating and Storage Junction Temperature
 Thermal Resistance

SYMBOL	2N6050	2N6051	2N6052	UNITS
	2N6057	2N6058	2N6059	
V_{CB0}	60	80	100	V
V_{CEO}	60	80	100	V
V_{EBO}		5.0		V
I_C		12		A
I_{CM}		20		A
I_B		0.2		A
P_D		150		W
T_J, T_{stg}		-65 to +200		$^\circ\text{C}$
θ_{JC}		1.17		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

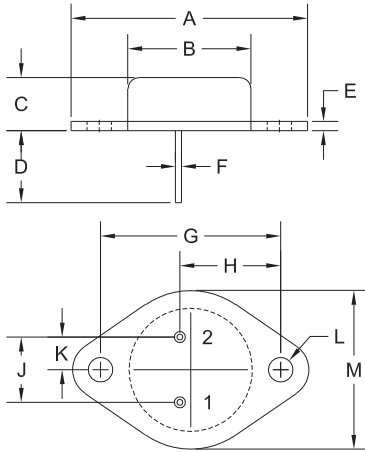
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CEV}	$V_{CE}=\text{Rated } V_{CEO}, V_{EB}=1.5\text{V}$		0.5	mA
I_{CEV}	$V_{CE}=\text{Rated } V_{CEO}, V_{EB}=1.5\text{V}, T_C=150^\circ\text{C}$		5.0	mA
I_{CEO}	$V_{CE}=\frac{1}{2}\text{Rated } V_{CEO}$		1.0	mA
I_{EBO}	$V_{EB}=5.0\text{V}$		2.0	mA
BV_{CEO}	$I_C=100\text{mA}, (2\text{N}6050, 2\text{N}6057)$	60		V
BV_{CEO}	$I_C=100\text{mA}, (2\text{N}6051, 2\text{N}6058)$	80		V
BV_{CEO}	$I_C=100\text{mA}, (2\text{N}6052, 2\text{N}6059)$	100		V
$V_{CE(\text{SAT})}$	$I_C=6.0\text{A}, I_B=24\text{mA}$		2.0	V
$V_{CE(\text{SAT})}$	$I_C=12\text{A}, I_B=120\text{mA}$		3.0	V
$V_{BE(\text{SAT})}$	$I_C=12\text{A}, I_B=120\text{mA}$		4.0	V
$V_{BE(\text{ON})}$	$V_{CE}=3.0\text{V}, I_C=6.0\text{A}$		2.8	V
h_{FE}	$V_{CE}=3.0\text{V}, I_C=6.0\text{A}$	750	18K	
h_{FE}	$V_{CE}=3.0\text{V}, I_C=12\text{A}$	100		
h_{fe}	$V_{CE}=3.0\text{V}, I_C=5.0\text{A}, f=1.0\text{kHz}$	300		
f_T	$V_{CE}=3.0\text{V}, I_C=5.0\text{A}, f=1.0\text{MHz}$	4.0		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$ (PNP types)		500	pF
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$ (NPN types)		300	pF

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TO-3 CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.516	1.573	38.50	39.96
B (DIA)	0.748	0.875	19.00	22.23
C	0.250	0.450	6.35	11.43
D	0.433	0.516	11.00	13.10
E	0.054	0.065	1.38	1.65
F	0.035	0.045	0.90	1.15
G	1.177	1.197	29.90	30.40
H	0.650	0.681	16.50	17.30
J	0.420	0.440	10.67	11.18
K	0.205	0.225	5.21	5.72
L (DIA)	0.151	0.172	3.84	4.36
M	0.984	1.050	25.00	26.67

TO-3 (REV: R2)

R2

LEAD CODE:

- 1) Base
- 2) Emitter
- Case) Collector

MARKING:

FULL PART NUMBER

R1 (18-September 2012)